

FDW6923

P-Channel 2.5V Specified PowerTrench® MOSFET with Schottky Diode

General Description

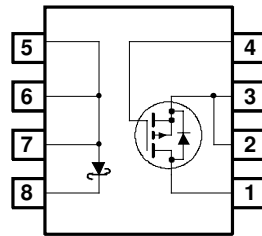
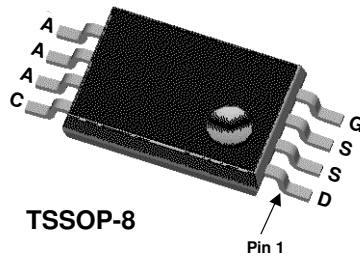
This P-Channel 2.5V specified MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It is combined with a low forward drop Schottky diode which is isolated from the MOSFET, providing a compact power solution for asynchronous DC/DC converter applications.

Applications

- DC/DC conversion

Features

- -3.5 A, -20 V. $R_{DS(ON)} = 0.045 \Omega @ V_{GS} = -4.5 V$
 $R_{DS(ON)} = 0.075 \Omega @ V_{GS} = -2.5 V$
- $V_F < 0.55 V @ 1 A$
- High performance trench technology for extremely low $R_{DS(ON)}$
- Low profile TSSOP-8 package



MOSFET Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	V
I_D	Drain Current – Continuous (Note 1)	-3.5	A
	– Pulsed	-30	
P_D	MOSFET Power Dissipation (minimum pad) (Note 1)	1.2	W
	Schottky Power Dissipation (minimum pad) (Note 1)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Schottky Maximum Ratings

V_{RRM}	Repetitive Peak Reverse Voltage	20	V
I_F	Average Forward Current	1.5	A
I_{FM}	Peak Forward Current	30	A

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (minimum pad) (Note 1)	MOSFET: 115 Schottky: 130	$^\circ C/W$
-----------------	--	------------------------------	--------------

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
6923	FDW6923	13"	16mm	2500 units

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		-16		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			100	nA

On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.6	-1.0	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C		3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_D = -3.5\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -2.7\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -3.5\text{ A}, T_J = 125^\circ\text{C}$		36 56 49	45 75 72	m Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-15			A
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -3.5\text{ A}$		13.2		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}$		1030		pF
C_{oss}	Output Capacitance	$f = 1.0\text{ MHz}$		280		pF
C_{riss}	Reverse Transfer Capacitance			120		pF

Switching Characteristics (Note 2)

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -5\text{ V}, I_D = -1\text{ A}$		11	20	ns
t_r	Turn–On Rise Time	$V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		18	32	ns
$t_{d(off)}$	Turn–Off Delay Time			34	55	ns
t_f	Turn–Off Fall Time			34	55	ns
Q_g	Total Gate Charge	$V_{DS} = -5\text{ V}, I_D = -3.5\text{ A}$		9.7	16	nC
Q_{gs}	Gate–Source Charge	$V_{GS} = -4.5\text{ V}$		2.2		nC
Q_{gd}	Gate–Drain Charge			2.4		nC

Drain–Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain–Source Diode Forward Current				-1.25	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1.25\text{ A}$ (Note 2)	-0.6		-1.2	V
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			100	nA

Schottky Diode Characteristics

I_R	Reverse Leakage	$V_R = 20\text{ V}$	$T_J = 25^\circ\text{C}$	0.6	50	μA
			$T_J = 125^\circ\text{C}$	1	8	mA
V_F	Forward Voltage	$I_F = 1\text{ A}$	$T_J = 25^\circ\text{C}$	0.48	0.55	V
			$T_J = 125^\circ\text{C}$	0.42	0.50	V
C_T	Junction Capacitance	$V_R = 10\text{ V}$		50		pF

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

$R_{\theta JA}$ is 115 $^\circ\text{C}/\text{W}$ for the MOSFET and 130 $^\circ\text{C}/\text{W}$ for the Schottky Diode when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

Typical Characteristics

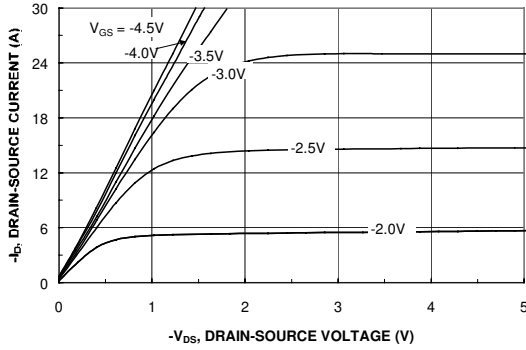


Figure 1. On-Region Characteristics.

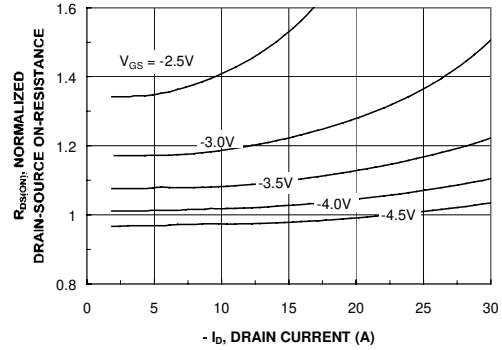


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

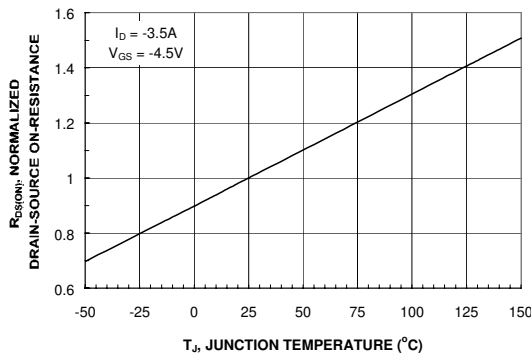


Figure 3. On-Resistance Variation with Temperature.

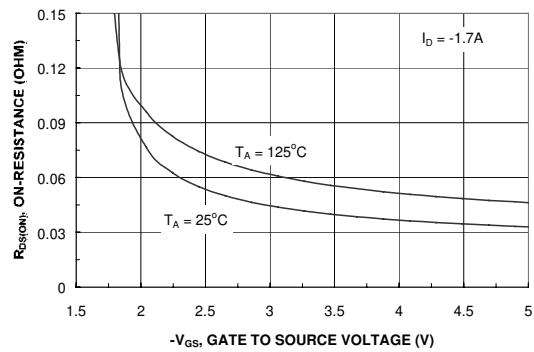


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

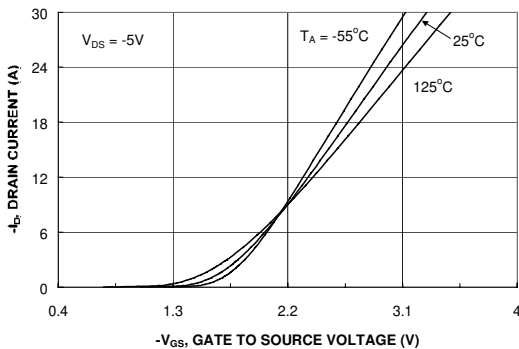


Figure 5. Transfer Characteristics.

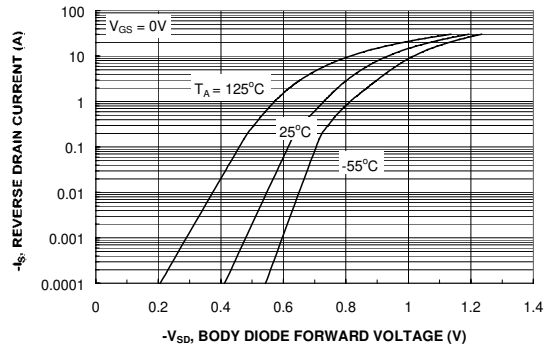


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

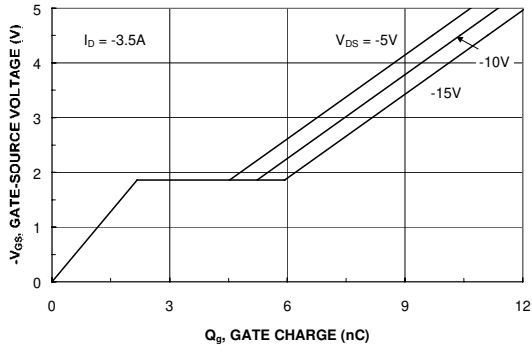


Figure 7. Gate Charge Characteristics.

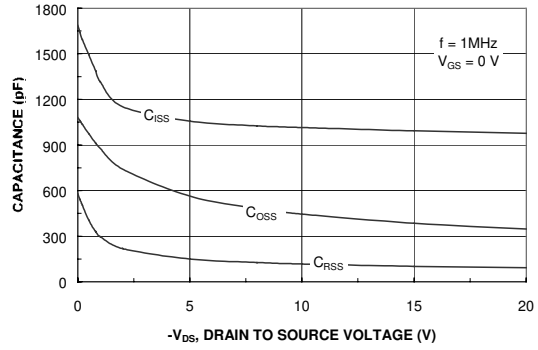


Figure 8. Capacitance Characteristics.

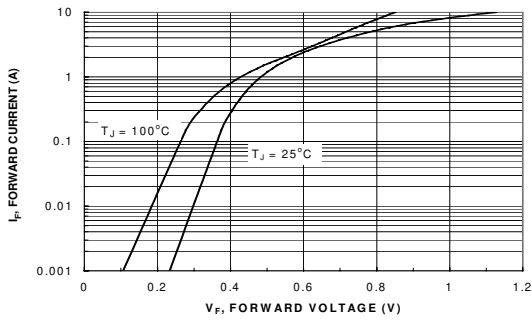


Figure 9. Schottky Diode Forward Voltage.

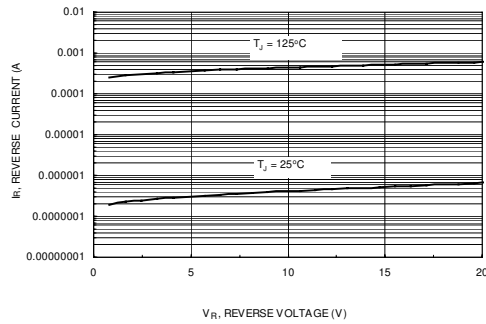


Figure 10. Schottky Diode Reverse Current.

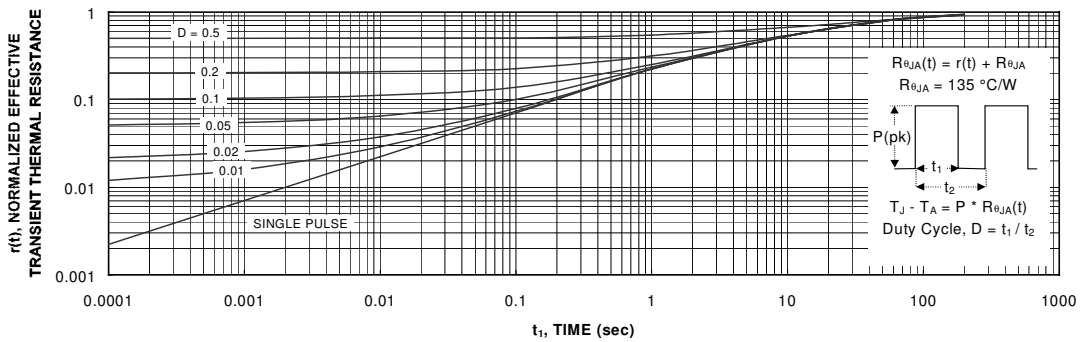


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1.
 Transient thermal response will change depending on the circuit board design.



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
EcoSPARK®
EfficientMax™
EZSWITCH™ *
™
™
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FlashWriter® *

FPS™
F-PFS™
FRFET®
Global Power ResourceSM
Green FPS™
Green FPS™ e-Series™
GTO™
IntelliMAX™
ISOPLANAR™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MillerDrive™
MotionMax™
Motion-SPM™
OPTOLOGIC®
OPTOPLANAR®

PDP SPM™
Power-SPM™
PowerTrench®
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
Saving our world, 1mW at a time™
SmartMax™
SMART START™
SPM®
STEALTH™
SuperFET™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SuperMOS™
SyncFET™

The Power Franchise®
the
power
franchise
TinyBoost™
TinyBuck™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™



* EZSWITCH™ and FlashWriter® are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.